

BDX34/A/B/C

Power Linear and Switching Applications

- High Gain General Purpose
- Power Darlington TR
- Complement to BDX33/33A/33B/33C respectively



1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

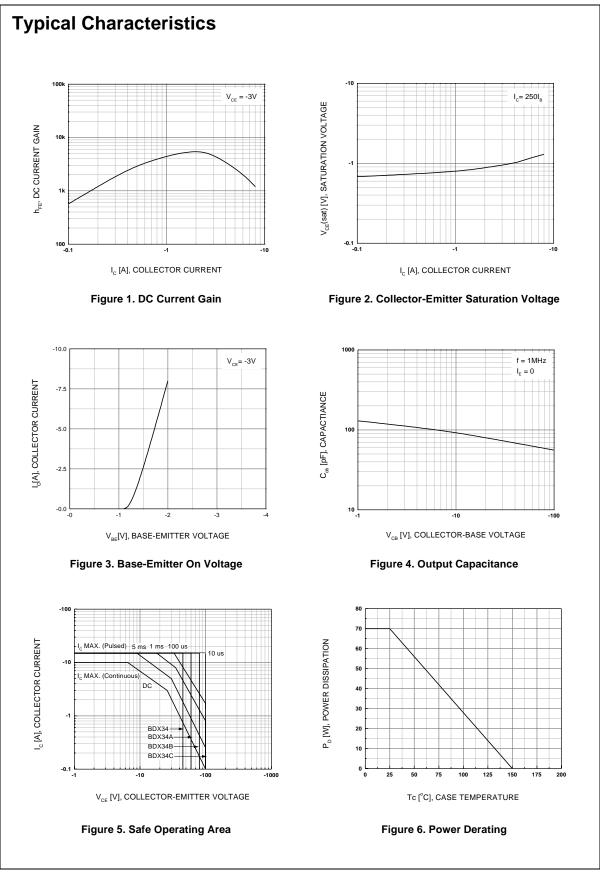
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: BDX34	- 45	V
	: BDX34A	- 60	V
	: BDX34B	- 80	V
	: BDX34C	- 100	V
V_{CEO}	Collector-Emitter Voltage		
	: BDX34	- 45	V
	: BDX34A	- 60	V
	: BDX34B	- 80	V
	: BDX34C	- 100	V
I _C	Collector Current (DC)	- 10	Α
I _{CP}	*Collector Current (Pulse)	- 15	А
l _B	Base Current	- 0.25	А
P _C	Collector Dissipation (T _C =25°C)	70	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B	I _C = -100mA, I _B = 0	- 45 - 60 - 80			V V V
	: BDX34C		- 100			V
V _{CER} (sus)	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B : BDX34C	$I_C = -1 \text{ 00mA}, I_B = 0$ $R_{BE} = 100\Omega$	- 45 - 60 - 80 - 100			V V V
V _{CEV} (sus)	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B : BDX34C	I _C = - 100mA, I _B = 0 V _{BE} = - 1.5V	- 45 - 60 - 80 - 100			V V V
I _{CBO}	Collector Cut-off Current : BDX34 : BDX34A : BDX34B : BDX34C	$V_{CB} = -45V, I_{E} = 0$ $V_{CB} = -60V, I_{E} = 0$ $V_{CB} = -80V, I_{E} = 0$ $V_{CB} = -100V, I_{E} = 0$			- 0.2 - 0.2 - 0.2 - 0.2	mA mA mA
I _{CEO}	Collector Cut-off Current : BDX34 : BDX34A : BDX34B : BDX34C	$V_{CE} = -22V, I_{B} = 0$ $V_{CE} = -30V, I_{B} = 0$ $V_{CE} = -40V, I_{B} = 0$ $V_{CE} = -50V, I_{B} = 0$			- 0.5 - 0.5 - 0.5 - 0.5	mA mA mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 5	mA
h _{FE}	* DC Current Gain : BDX34/34A : BDX34B/34C	V _{CE} = - 3V, I _C = - 4A V _{CE} = - 3V, I _C = - 3A	750 750			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage : BDX34/34A : BDX34B/34C	I _C = - 4A, I _B = - 8mA I _C = - 3A, I _B = - 6mA			- 2.5 - 2.5	V
V _{BE} (on)	* Base-Emitter ON Voltage : BDX34/34A : BDX34B/34C	$V_{CE} = -3V, I_{C} = -4A$ $V_{CE} = -3V, I_{C} = -3A$			- 2.5 - 2.5	V

I_F = - 8A

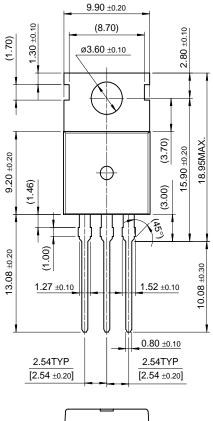
V_F * Parallel Diode Forward Voltage * Pulse Test: PW=300μs, duty Cycle =1.5% Pulsed

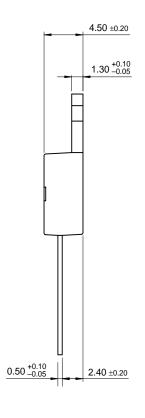


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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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